

NPN SILICON RF TRANSISTOR

DESCRIPTION:

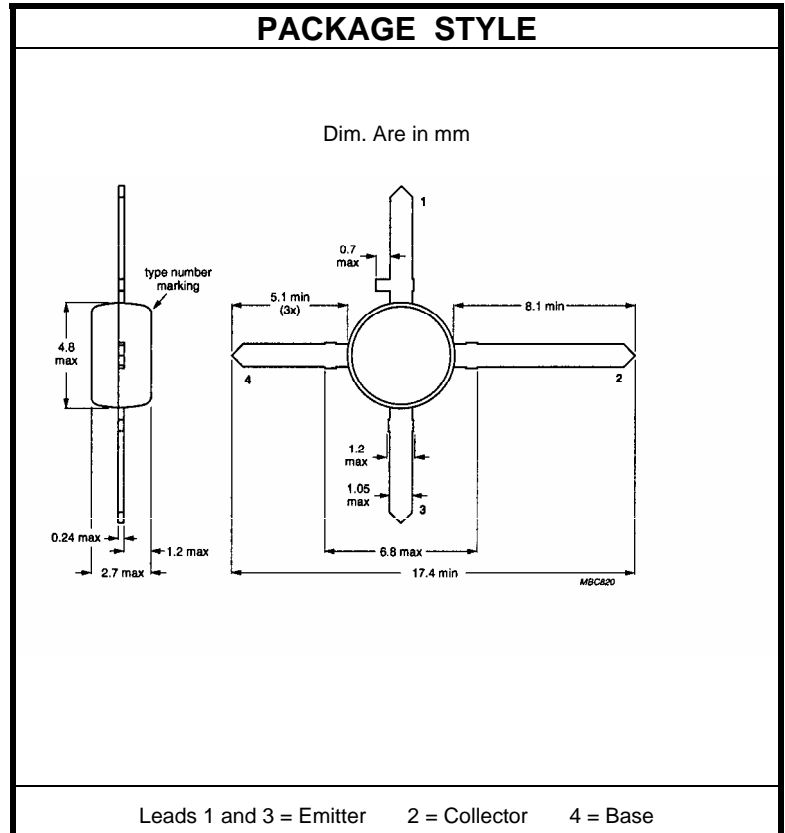
The **MRF581** is Designed for
High current low Power Amplifier
Applications up to 1.0 GHz.

FEATURES:

- Low Noise Figure
- Low Intermodulation Distortion
- High Gain
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	200 mA
V_{CB0}	36 V
V_{CEO}	18 V
V_{EBO}	2.5 V
P_{DISS}	2.5 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +200 °C


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CB0}	I _C = 1.0 mA		36			V
BV_{CEO}	I _C = 1.0 mA		18			V
BV_{EBO}	I _E = 100 μA		2.5			V
I_{EBO}	V _{EB} = 2.0 V				100	μA
I_{CB0}	V _{CB} = 15 V				100	μA
h_{FE}	V _{CE} = 5.0 V	I _C = 50 mA	50		200	---
C_{cb}	V _{CB} = 10 V	f = 1.0 MHz		1.4	2.0	pF
G_P	V _{CC} = 10 V	I _C = 50	13	15.5		dB